

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX16373FT

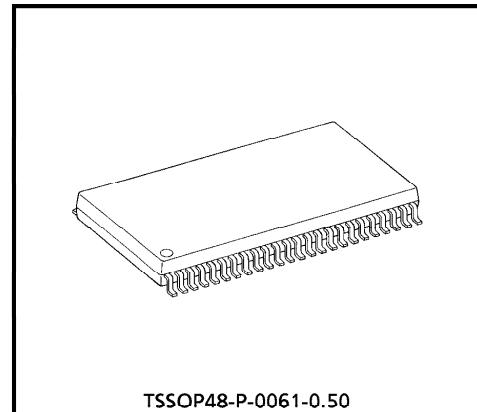
LOW-VOLTAGE 16-BIT D-TYPE LATCH WITH 3.6V TOLERANT INPUTS AND OUTPUTS

The TC74VCX16373FT is a high performance CMOS 16-bit D-TYPE LATCH. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6V.

This 16-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the \overline{OE} input is high, the outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight : 0.25g (Typ.)

PIN CONNECTION

1	\overline{OE}	48	1LE
2	1Q1	47	1D1
3	1Q2	46	1D2
4	GND	45	GND
5	1Q3	44	1D3
6	1Q4	43	1D4
7	VCC	42	VCC
8	1Q5	41	1D5
9	1Q6	40	1D6
10	GND	39	GND
11	1Q7	38	1D7
12	1Q8	37	1D8
13	2Q1	36	2D1
14	2Q2	35	2D2
15	GND	34	GND
16	2Q3	33	2D3
17	2Q4	32	2D4
18	VCC	31	VCC
19	2Q5	30	2D5
20	2Q6	29	2D6
21	GND	28	GND
22	2Q7	27	2D7
23	2Q8	26	2D8
24	2OE	25	2LE

(TOP VIEW)

FEATURES

- Low Voltage Operation : $V_{CC} = 1.8 \sim 3.6V$
- High Speed Operation : $t_{pd} = 3.0\text{ns}$ (max.) at $V_{CC} = 3.0 \sim 3.6V$
 : $t_{pd} = 3.4\text{ns}$ (max.) at $V_{CC} = 2.3 \sim 2.7V$
 : $t_{pd} = 6.0\text{ns}$ (max.) at $V_{CC} = 1.8V$
- 3.6V Tolerant inputs and outputs.
- Output Current : $I_{OH}/I_{OL} = \pm 24\text{mA}$ (min.) at $V_{CC} = 3.0V$
 : $I_{OH}/I_{OL} = \pm 18\text{mA}$ (min.) at $V_{CC} = 2.3V$
 : $I_{OH}/I_{OL} = \pm 6\text{mA}$ (min.) at $V_{CC} = 1.8V$
- Latch-up Performance : $\pm 300\text{mA}$
- ESD Performance : Human Body Model $> \pm 2000V$
 : Machine Model $> 200V$
- Package : TSSOP
 (Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.

961001EBA2

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TRUTH TABLE

INPUT		OUTPUT	
$1\overline{OE}$	$1LE$	$1D1-1D8$	$1Q1-1Q8$
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

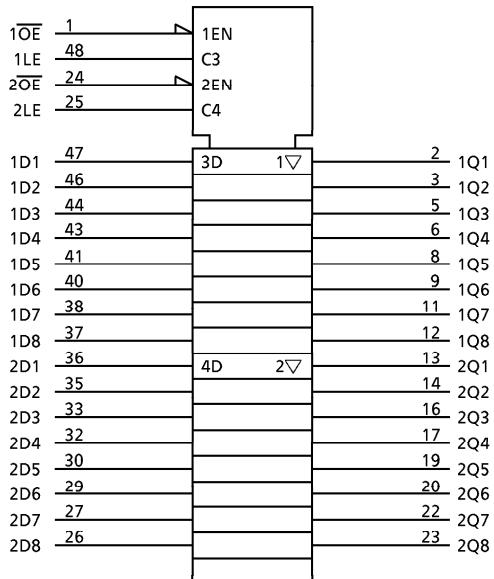
INPUT		OUTPUT	
$2\overline{OE}$	$2LE$	$2D1-2D8$	$2Q1-2Q8$
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X : Don't Care

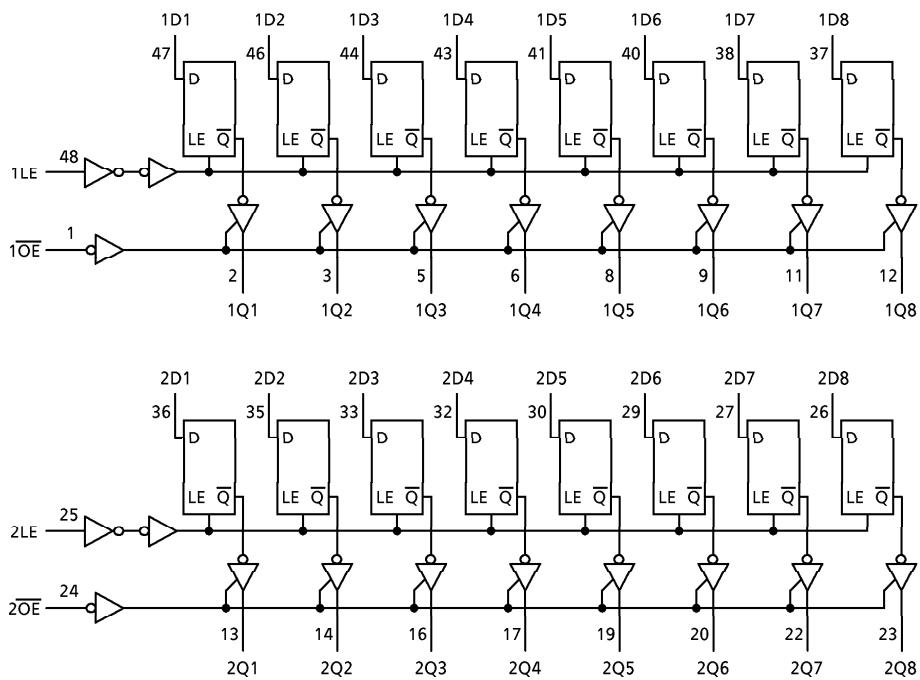
Z : High impedance

 Q_n : No change

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



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MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~4.6	V
DC Input Voltage	V_{IN}	-0.5~4.6	V
DC Output Voltage	V_{OUT}	-0.5~4.6 (Note 1)	V
		-0.5~ V_{CC} +0.5 (Note 2)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	± 50 (Note 3)	mA
DC Output Current	I_{OUT}	± 50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC} / I_{GND}	± 100	mA
Storage Temperature	T_{stg}	-65~150	°C

(Note 1) Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	V_{OUT}	0~3.6 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH} / I_{OL}	± 24 (Note 7)	mA
		± 18 (Note 8)	
		± 6 (Note 9)	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt / dv	0~10 (Note 10)	ns/V

(Note 4) Data Retention Only

(Note 5) Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0 \sim 3.6V$ (Note 8) $V_{CC} = 2.3 \sim 2.7V$ (Note 9) $V_{CC} = 1.8V$ (Note 10) $V_{IN} = 0.8 \sim 2.0V$, $V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICSDC characteristics ($T_a = -40\sim85^\circ C$, $2.7V < V_{CC} \leq 3.6V$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V_{IH}			2.7~3.6	2.0	—	V	
	"L" Level	V_{IL}			2.7~3.6	—	0.8	V	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100\mu A$	2.7~3.6	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -12mA$	2.7	2.2	—		
				$I_{OH} = -18mA$	3.0	2.4	—		
				$I_{OH} = -24mA$	3.0	2.2	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100\mu A$	2.7~3.6	—	0.2	V	
				$I_{OL} = 12mA$	2.7	—	0.4		
				$I_{OL} = 18mA$	3.0	—	0.4		
				$I_{OL} = 24mA$	3.0	—	0.55		
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 3.6V$		2.7~3.6	—	± 5.0	μA		
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\sim 3.6V$		2.7~3.6	—	± 10.0	μA		
Power Off Leakage Current	I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6V$		0	—	10.0	μA		
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND	2.7~3.6	—	20.0	μA		
$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V$			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V$	2.7~3.6	—	± 20.0			
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6V$		2.7~3.6	—	750	μA		

ELECTRICAL CHARACTERISTICSDC characteristics ($T_a = -40\sim85^\circ C$, $2.3V \leq V_{CC} \leq 2.7V$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT	
Input Voltage	"H" Level	V_{IH}			2.3~2.7	1.6	—	V	
	"L" Level	V_{IL}			2.3~2.7	—	0.7	V	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100\mu A$	2.3~2.7	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6mA$	2.3	2.0	—		
				$I_{OH} = -12mA$	2.3	1.8	—		
				$I_{OH} = -18mA$	2.3	1.7	—		
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100\mu A$	2.3~2.7	—	0.2	V	
				$I_{OL} = 12mA$	2.3	—	0.4		
				$I_{OL} = 18mA$	2.3	—	0.6		
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 3.6V$		2.3~2.7	—	± 5.0	μA		
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0\sim 3.6V$		2.3~2.7	—	± 10.0	μA		
Power Off Leakage Current	I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6V$		0	—	10.0	μA		
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND	2.3~2.7	—	20.0	μA		
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V_{CC}$	2.3~2.7	—	± 20.0			

ELECTRICAL CHARACTERISTICSDC characteristics ($T_a = -40 \sim 85^\circ C$, $1.8V \leq V_{CC} < 2.3V$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V_{IH}			1.8~2.3	$0.7 \times V_{CC}$	—	V
	"L" Level	V_{IL}			1.8~2.3	—	$0.2 \times V_{CC}$	V
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100\mu A$ $I_{OH} = -6mA$	1.8	$V_{CC} - 0.2$	—	V
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100\mu A$ $I_{OL} = 6mA$	1.8	1.4	—	V
Input Leakage Current	I_{IN}	$V_{IN} = 0 \sim 3.6V$			1.8	—	± 5.0	μA
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6V$			1.8	—	± 10.0	μA
Power Off Leakage Current	I_{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6V$			0	—	10.0	μA
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND $V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V$		1.8	—	20.0	μA
					1.8	—	± 20.0	

AC characteristics ($T_a = -40\sim85^\circ C$, Input $t_r=t_f=2.0\text{ns}$, $C_L=30\text{pF}$, $R_L=500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	MIN.	MAX.	UNIT
			1.8			
Propagation Delay Time (D-Q)	t_{pLH} t_{pHL}	(Fig.1, 2)	2.5 ± 0.2	1.0	3.4	ns
			3.3 ± 0.3	0.8	3.0	
			1.8	1.5	6.0	
Propagation Delay Time (LE-Q)	t_{pLH} t_{pHL}	(Fig.1, 2)	2.5 ± 0.2	1.0	3.9	ns
			3.3 ± 0.3	0.8	3.1	
			1.8	1.5	7.0	
3-State Output Enable Time	t_{pZL} t_{pZH}	(Fig.1, 3)	2.5 ± 0.2	1.0	4.6	ns
			3.3 ± 0.3	0.8	3.5	
			1.8	1.5	5.0	
3-State Output Disable Time	t_{pLZ} t_{pHZ}	(Fig.1, 3)	2.5 ± 0.2	1.0	3.8	ns
			3.3 ± 0.3	0.8	3.5	
			1.8	3.0	—	
Minimum Pulse Width (LE)	$t_w(\text{H})$	(Fig.1, 2)	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	2.5	—	
Minimum Set-up Time	t_s	(Fig.1, 2)	2.5 ± 0.2	1.5	—	ns
			3.3 ± 0.3	1.5	—	
			1.8	1.0	—	
Minimum Hold Time	t_h	(Fig.1, 2)	2.5 ± 0.2	1.0	—	ns
			3.3 ± 0.3	1.0	—	
			1.8	—	0.5	
Output To Output Skew	t_{osLH} t_{osHL}	(Note 11)	2.5 ± 0.2	—	0.5	ns
			3.3 ± 0.3	—	0.5	
			1.8	—	0.5	

For $C_L=50\text{pF}$, add approximately 300ps to the AC maximum specification.

(Note 11) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics ($T_a = 25^\circ\text{C}$, Input $t_r = t_f = 2.0\text{ns}$, $C_L = 30\text{pF}$, $R_L = 500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	TYP.	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$V_{IH} = 1.8\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	1.8	0.25	V
		$V_{IH} = 2.5\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	2.5	0.6	
		$V_{IH} = 3.3\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	3.3	0.8	
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	$V_{IH} = 1.8\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	1.8	-0.25	V
		$V_{IH} = 2.5\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	2.5	-0.6	
		$V_{IH} = 3.3\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	3.3	-0.8	
Quiet Output Minimum Dynamic V_{OH}	V_{OHV}	$V_{IH} = 1.8\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	1.8	1.5	V
		$V_{IH} = 2.5\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	2.5	1.9	
		$V_{IH} = 3.3\text{V}$, $V_{IL} = 0\text{V}$ (Note 12)	3.3	2.2	

(Note 12) Parameter guaranteed by design.

Capacitive characteristics ($T_a = 25^\circ\text{C}$)

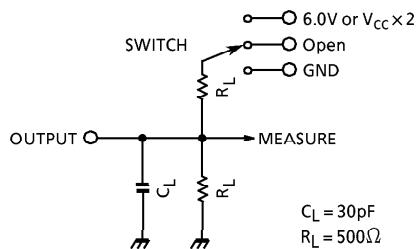
PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	TYP.	UNIT
Input Capacitance	C_{IN}		1.8, 2.5, 3.3	6	pF
Output Capacitance	C_O		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C_{PD}	$f_{IN} = 10\text{MHz}$ (Note 13)	1.8, 2.5, 3.3	20	pF

(Note 13) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16 \text{ (per bit)}$$

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	$6.0\text{V} @ V_{CC} = 3.3 \pm 0.3\text{V}$ $V_{CC}\times 2 @ V_{CC} = 2.5 \pm 0.2\text{V}$ $@ V_{CC} = 1.8\text{V}$
t_{pHZ}, t_{pZH}	GND

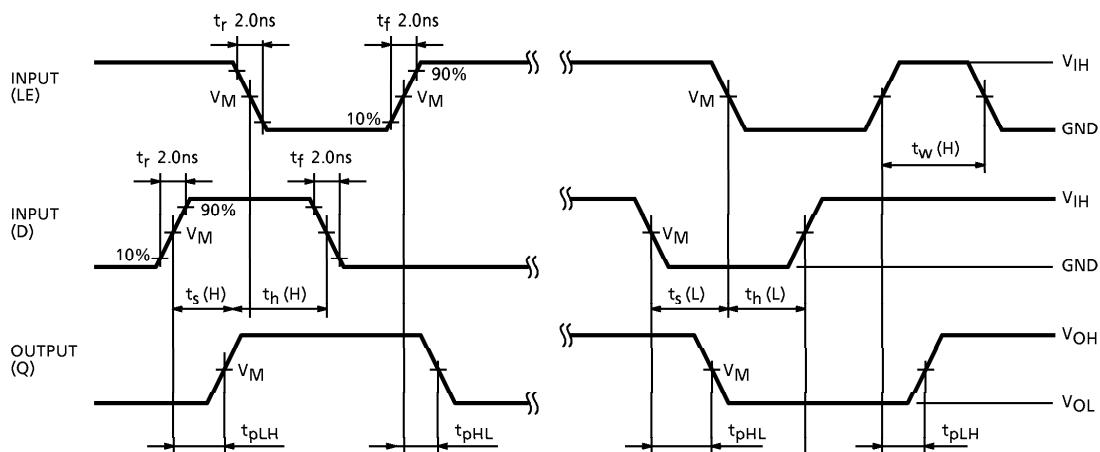
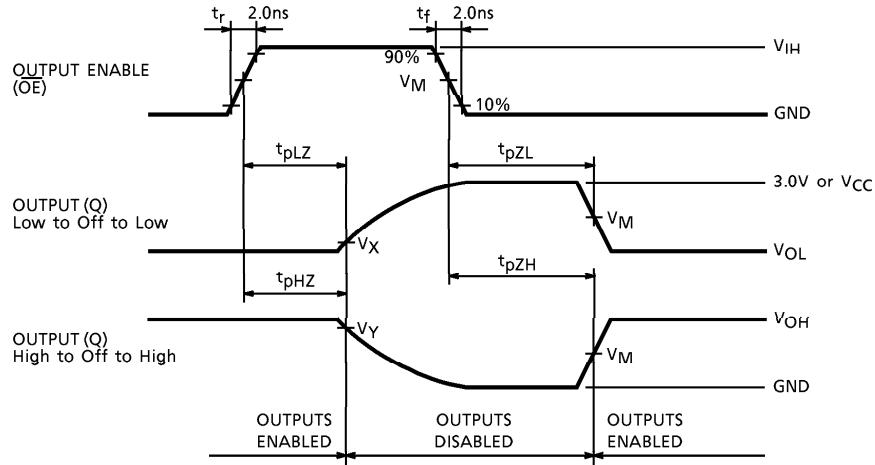
AC WAVEFORMFig.2 t_{pLH} , t_{pHL} , t_w , t_s , t_h 

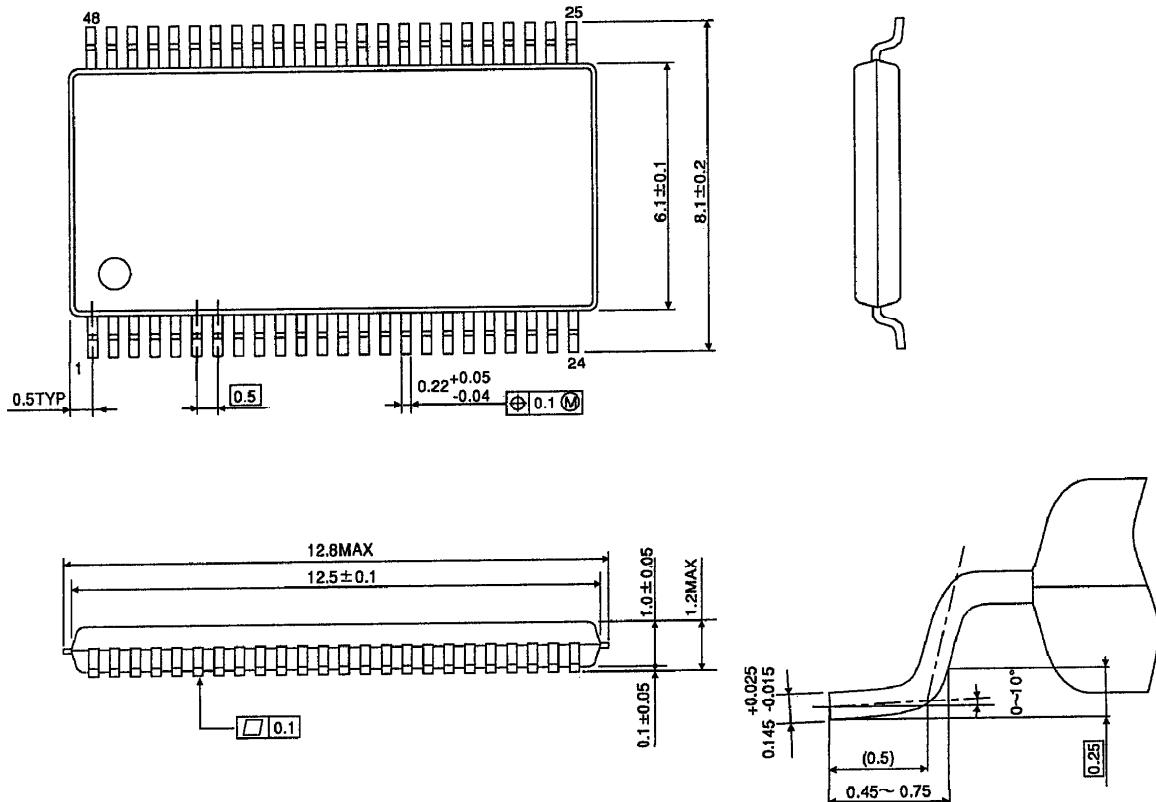
Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH} 

SYMBOL	V_{CC}		
	$3.3 \pm 0.3V$	$2.5 \pm 0.2V$	$1.8V$
V_{IH}	2.7V	V_{CC}	V_{CC}
V_M	1.5V	$V_{CC} / 2$	$V_{CC} / 2$
V_X	$V_{OL} + 0.3V$	$V_{OL} + 0.15V$	$V_{OL} + 0.15V$
V_Y	$V_{OH} - 0.3V$	$V_{OH} - 0.15V$	$V_{OH} - 0.15V$

OUTLINE DRAWING

TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25g (Typ.)